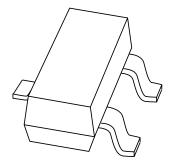
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# **BF862**N-channel junction FET

Product specification Supersedes data of 1999 Jun 29

2000 Jan 05



# **N-channel junction FET**

**BF862** 

#### **FEATURES**

- High transition frequency for excellent sensitivity in AM car radios
- High transfer admittance.

#### **APPLICATIONS**

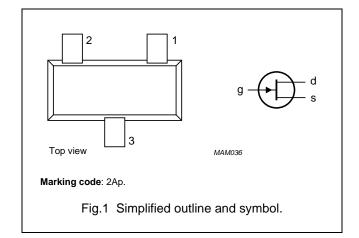
• Pre-amplifiers in AM car radios.

#### **DESCRIPTION**

Silicon N-channel symmetrical junction field-effect transistor in a SOT23 package. Drain and source are interchangeable.

#### **PINNING SOT23**

PIN	DESCRIPTION
1	source
2	drain
3	gate



#### **QUICK REFERENCE DATA**

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>DS</sub>	drain-source voltage		_	_	20	V
$V_{GSoff}$	gate-source cut-off voltage		-0.3	-0.8	-1.2	V
I <sub>DSS</sub>	drain-source current		10	_	25	mA
P <sub>tot</sub>	total power dissipation	T <sub>s</sub> ≤ 90 °C	_	_	300	mW
y <sub>fs</sub>	transfer admittance		35	45	_	mS
T <sub>j</sub>	junction temperature		_	_	150	°C

#### **CAUTION**

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling.

# N-channel junction FET

BF862

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>DS</sub>	drain-source voltage		_	20	V
$V_{DG}$	drain-gate voltage		_	20	V
$V_{GS}$	gate-source voltage		_	-20	V
I <sub>DS</sub>	drain-source current		_	40	mA
$I_{G}$	forward gate current		_	10	mA
P <sub>tot</sub>	total power dissipation	T <sub>s</sub> ≤ 90 °C; note 1	_	300	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	150	°C

#### Note

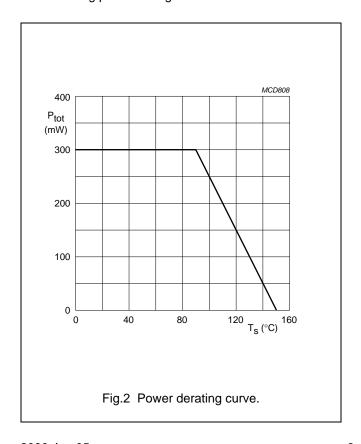
1. Main heat transfer is via the gate lead.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-s</sub>	thermal resistance from junction to soldering point	note 1	200	K/W

#### Note

1. Soldering point of the gate lead.



# N-channel junction FET

BF862

#### STATIC CHARACTERISTICS

 $T_j$  = 25 °C; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>(BR)GSS</sub>	gate-source breakdown voltage	$I_{GS} = -1 \mu A; V_{DS} = 0$	-20	_	_	V
$V_{GS}$	gate-source forward voltage	$V_{DS} = 0$ ; $I_{G} = 1 \text{ mA}$	_	_	1	V
$V_{GSoff}$	gate-source cut-off voltage	$V_{DS} = 8 \text{ V}; I_D = 1 \mu A$	-0.3	-0.8	-1.2	V
I <sub>GSS</sub>	reverse gate current	$V_{GS} = -15 \text{ V}; V_{DS} = 0$	_	_	-1	nA
I <sub>DSS</sub>	drain-source current	V <sub>GS</sub> = 0; V <sub>DS</sub> = 8 V	10	_	25	mA

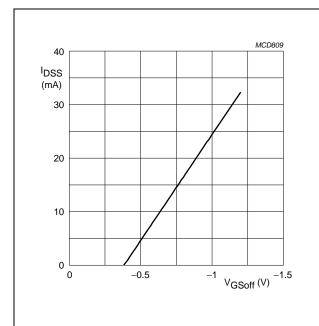
#### **DYNAMIC CHARACTERISTICS**

Common source;  $T_{amb}$  = 25 °C;  $V_{GS}$  = 0;  $V_{DS}$  = 8 V; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
y <sub>fs</sub>	common source forward transfer admittance	T <sub>j</sub> = 25 °C	35	45	_	mS
gos	common source output conductance	T <sub>j</sub> = 25 °C	_	180	400	μS
C <sub>iss</sub>	input capacitance	f = 1 MHz	_	10	_	pF
C <sub>rss</sub>	reverse transfer capacitance	f = 1 MHz	_	1.9	_	pF
e <sub>n</sub>	equivalent noise input voltage	f = 100 kHz	_	0.8	_	nV/√Hz
f <sub>T</sub>	transition frequency		_	715	_	MHz

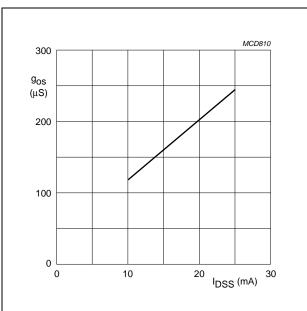
# N-channel junction FET

BF862



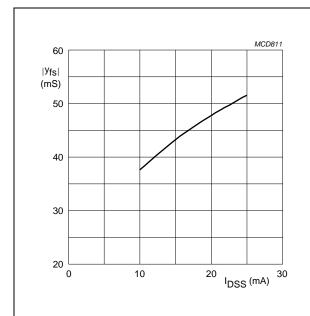
 $V_{DS}$  = 8 V;  $T_j$  = 25 °C.

Fig.3 Drain saturation current as a function of gate-source cut-off voltage; typical values.



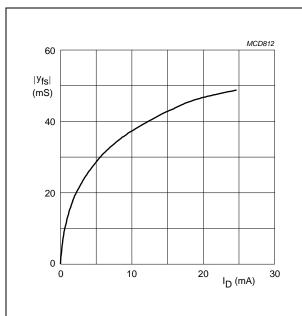
 $V_{DS}$  = 8 V;  $T_j$  = 25 °C.

Fig.4 Common-source output conductance as a function of drain saturation current; typical values.



 $V_{DS}$  = 8 V;  $T_j$  = 25 °C.

Fig.5 Forward transfer admittance as a function of drain saturation current; typical values.

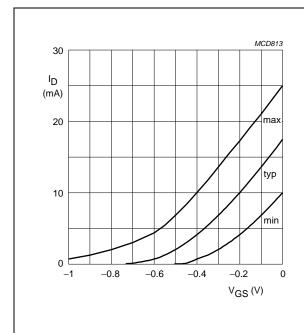


 $V_{DS}$  = 8 V;  $T_j$  = 25 °C.

Fig.6 Forward transfer admittance as a function of drain current; typical values.

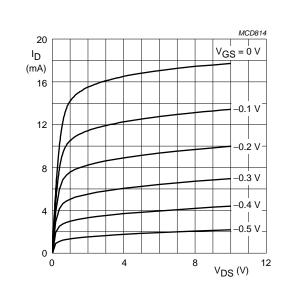
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BF862



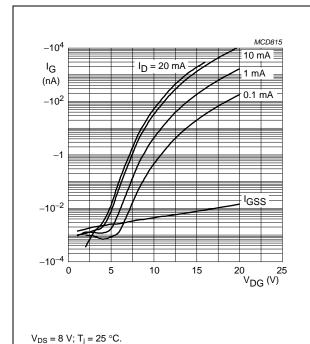
 $V_{DS}$  = 8 V;  $T_j$  = 25 °C.

Fig.7 Drain current as a function of gate-source voltage; typical values.



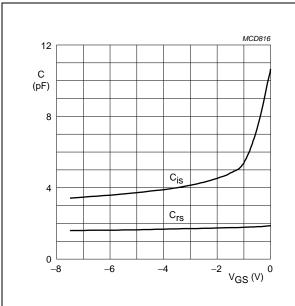
 $V_{DS} = 8 \text{ V}; T_j = 25 ^{\circ}\text{C}.$ 

Fig.8 Drain current as a function of drain-source voltage; typical values.



VDS = 0 V, 1j = 25 C.

Fig.9 Gate current as a function of drain-gate voltage; typical values.



 $V_{DS}$  = 8 V; f = 1 MHz;  $T_j$  = 25 °C.

Fig.10 Input and reverse transfer capacitance as functions of gate-source voltage; typical values.

# N-channel junction FET

BF862

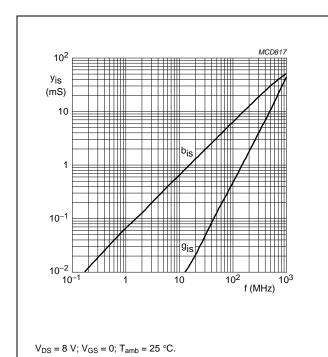
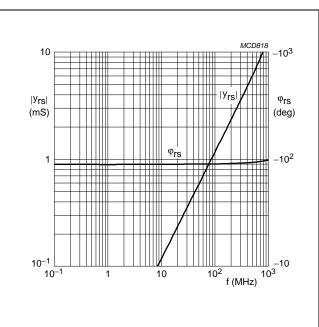
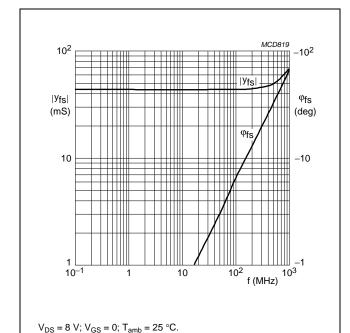


Fig.11 Common-source input admittance as a



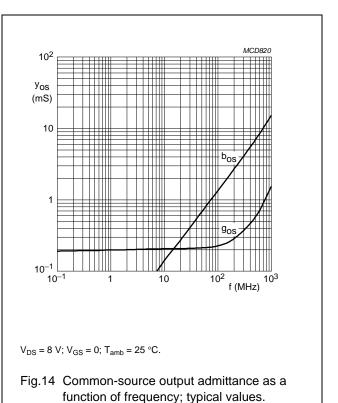
 $V_{DS} = 5 \text{ V}; V_{G2} = 4 \text{ V}.$  $I_{D} = 15 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}.$ 

Fig.12 Common-source reverse admittance as a function of frequency; typical values.



function of frequency; typical values.

Fig.13 Common-source forward transfer admittance as a function of frequency; typical values.



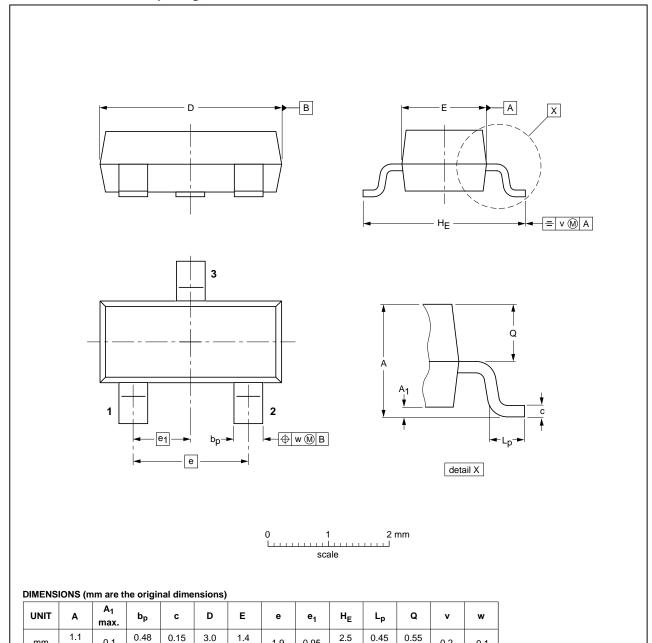
# N-channel junction FET

BF862

#### **PACKAGE OUTLINE**

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	1330E DATE
SOT23		TO-236AB				<del>-04-11-04</del> 06-03-16

0.95

1.9

0.1

0.2

2000 Jan 05 8

0.1

0.38

0.9

### N-channel junction FET

BF862

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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BF862

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#### **Contact information**

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